

NDD01N60, NDT01N60

N-Channel Power MOSFET 600 V, 8.5 Ω

Features

- 100% Avalanche Tested
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

ABSOLUTE MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	NDD	NDT	Unit
Drain-to-Source Voltage	V _{DSS}	600		V
Continuous Drain Current R _{θJC} Steady State, T _C = 25°C (Note 1)	I _D	1.5	0.4	A
Continuous Drain Current R _{θJC} Steady State, T _C = 100°C (Note 1)	I _D	1.0	0.25	A
Pulsed Drain Current, t _p = 10 μs	I _{DM}	6.0	1.5	A
Power Dissipation – R _{θJC} Steady State, T _C = 25°C	P _D	46	2.5	W
Gate-to-Source Voltage	V _{GS}	±30		V
Single Pulse Drain-to-Source Avalanche Energy (I _{PK} = 1.0 A)	EAS	13		mJ
Peak Diode Recovery (Note 2)	dv/dt	4.5		V/ns
Source Current (Body Diode)	I _S	1.5	0.4	A
Lead Temperature for Soldering Leads	T _L	260		°C
Operating Junction and Storage Temperature	T _J , T _{STG}	-55 to +150		°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Limited by maximum junction temperature
2. I_S = 1.5 A, di/dt ≤ 100 A/μs, V_{DD} ≤ BV_{DSS}

THERMAL RESISTANCE

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	R _{θJC}	2.7	°C/W
Junction-to-Ambient (Note 4) NDD01N60 (Note 3) NDD01N60-1 (Note 4) NDT01N60 (Note 5) NDT01N60	R _{θJA}	38	°C/W
		96	
		58	
		141	

3. Insertion mounted.
4. Surface-mounted on FR4 board using 1" sq. pad size (Cu area = 1.127" sq. [2 oz] including traces).
5. Surface-mounted on FR4 board using minimum recommended pad size (Cu area = 0.026" sq. [2 oz]).

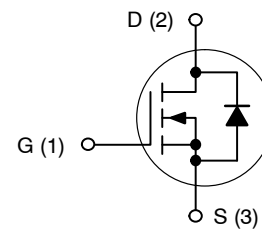


ON Semiconductor®

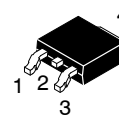
<http://onsemi.com>

V _{(BR)DSS}	R _{DS(ON)} MAX
600 V	8.5 Ω @ 10 V

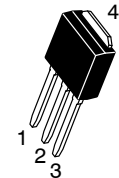
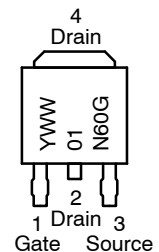
N-Channel MOSFET



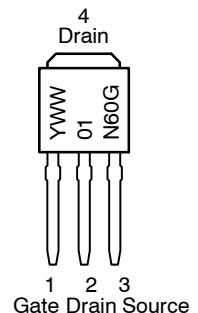
MARKING DIAGRAMS



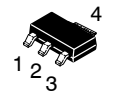
**DPAK
CASE 369C
STYLE 2**



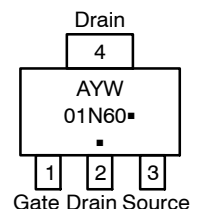
**IPAK
CASE 369D
STYLE 2**



Y = Year
WW = Work Week
G = Pb-Free Package



**SOT-223
CASE 318E
STYLE 3**



A = Assembly Location
Y = Year
W = Work Week
01N60 = Specific Device Code
■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

NDD01N60, NDT01N60

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
----------------	--------	-----------------	-----	-----	-----	------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 1 mA	600			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	Reference to 25°C, I _D = 1 mA		660		mV/°C
Drain-to-Source Leakage Current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	T _J = 25°C		1	μA
			T _J = 125°C		50	
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±20 V			±100	nA

ON CHARACTERISTICS (Note 6)

Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 50 μA	2.2	3.3	3.7	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			7.0		mV/°C
Static Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 0.2 A		8.0	8.5	Ω
Forward Transconductance	g _{FS}	V _{DS} = 15 V, I _D = 0.2 A		0.9		S

CHARGES, CAPACITANCES & GATE RESISTANCES

Input Capacitance (Note 7)	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		160		pF
Output Capacitance (Note 7)	C _{oss}			22		
Reverse Transfer Capacitance (Note 7)	C _{rss}			4.0		
Total Gate Charge (Note 7)	Q _g	V _{DS} = 300 V, I _D = 0.4 A, V _{GS} = 10 V		7.2		nC
Gate-to-Source Charge (Note 7)	Q _{gs}			1.2		
Gate-to-Drain Charge (Note 7)	Q _{gd}			3.1		
Plateau Voltage	V _{GP}			4.5		
Gate Resistance	R _g			6.7		Ω

SWITCHING CHARACTERISTICS (Note 8)

Turn-on Delay Time	t _{d(on)}	V _{DD} = 300 V, I _D = 0.4 A, V _{GS} = 10 V, R _G = 0 Ω		8.0		ns
Rise Time	t _r			5.1		
Turn-off Delay Time	t _{d(off)}			16.5		
Fall Time	t _f			21.3		

DRAIN-SOURCE DIODE CHARACTERISTICS

Diode Forward Voltage	V _{SD}	I _S = 0.4 A, V _{GS} = 0 V	T _J = 25°C	0.78	1.6	V
			T _J = 125°C	0.63		
Reverse Recovery Time	t _{rr}	V _{GS} = 0 V, V _{DD} = 30 V I _S = 1.0 A, d _i /d _t = 100 A/μs		179		ns
Charge Time	t _a			37		
Discharge Time	t _b			141		
Reverse Recovery Charge	Q _{rr}			288		

6. Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

7. Guaranteed by design.

8. Switching characteristics are independent of operating junction temperatures.

ORDERING INFORMATION

Device	Package	Shipping [†]
NDD01N60-1G	IPAK (Pb-Free, Halogen-Free)	75 Units / Rail
NDD01N60T4G	DPAK (Pb-Free, Halogen-Free)	2500 / Tape & Reel
NDT01N60T1G	SOT-223 (Pb-Free, Halogen-Free)	1000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NDD01N60, NDT01N60

TYPICAL CHARACTERISTICS

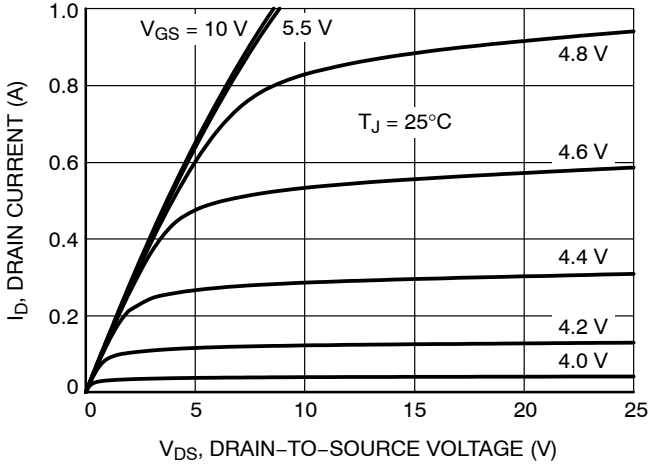


Figure 1. On-Region Characteristics

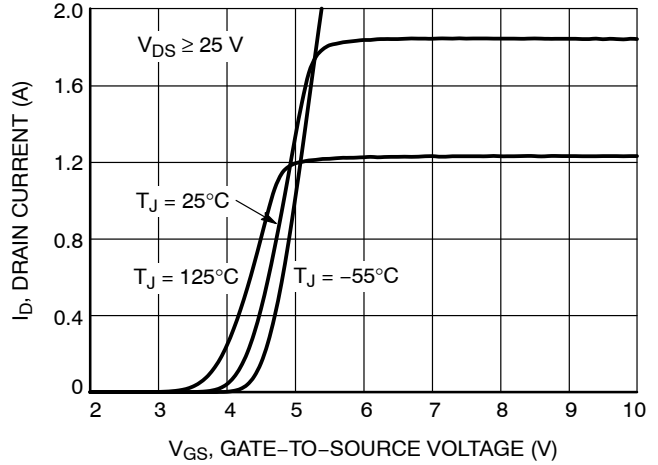


Figure 2. Transfer Characteristics

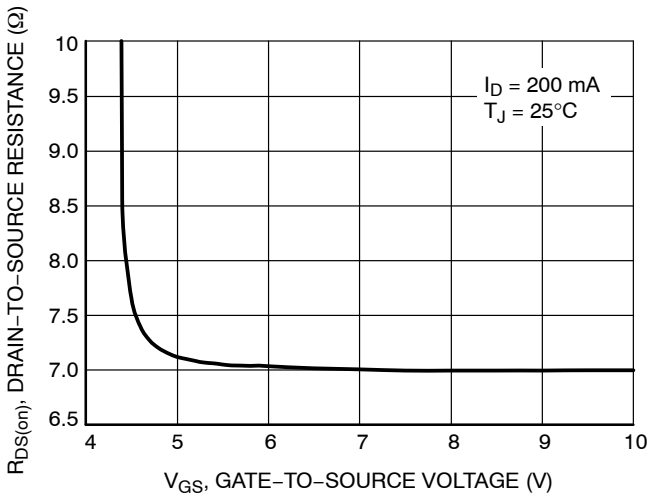


Figure 3. On-Resistance vs. Gate Voltage

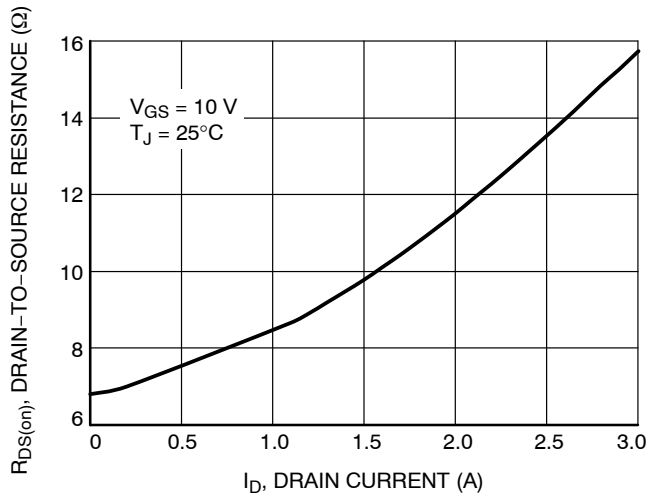


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

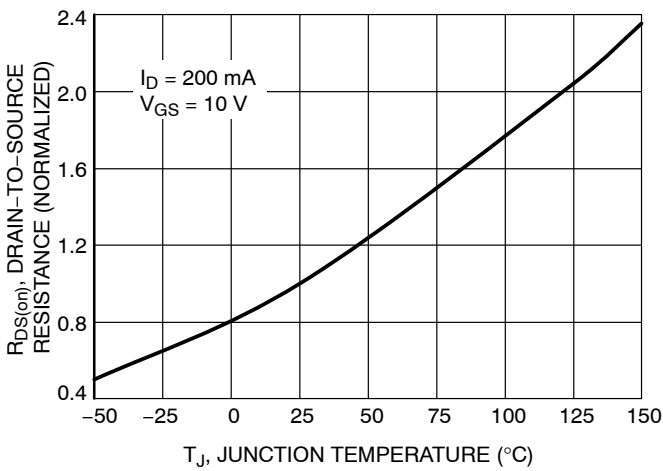


Figure 5. On-Resistance Variation with Temperature

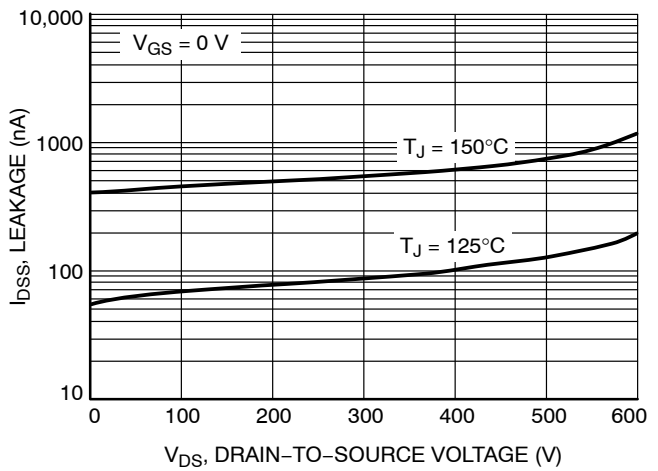


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NDD01N60, NDT01N60

TYPICAL CHARACTERISTICS

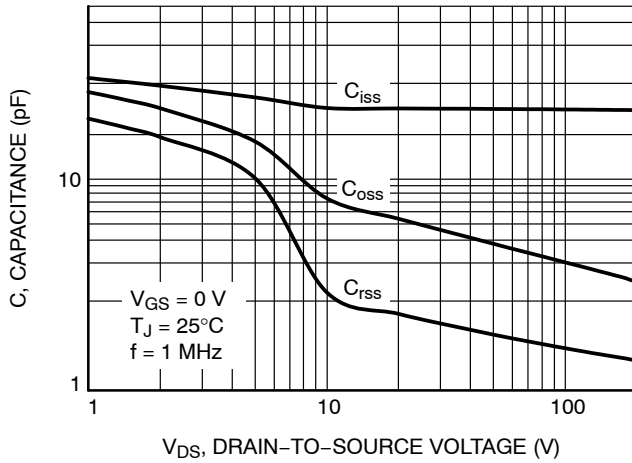


Figure 7. Capacitance Variation

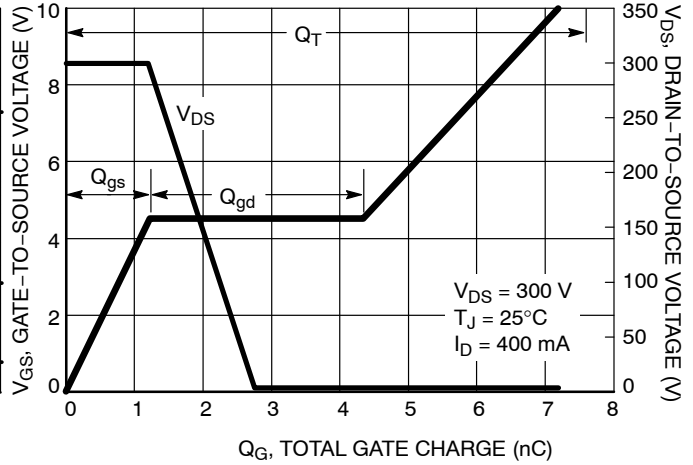


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

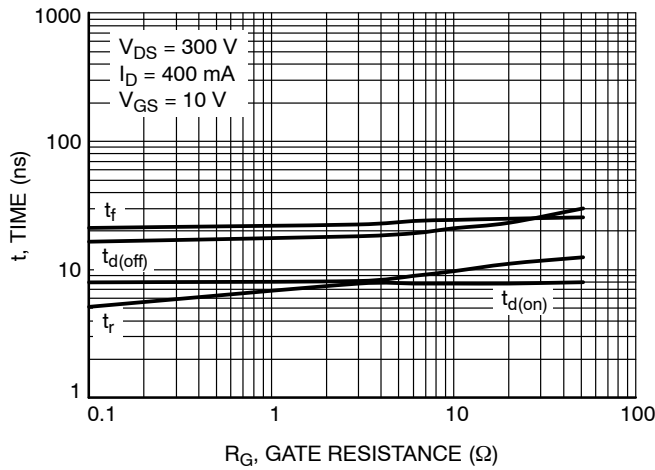


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

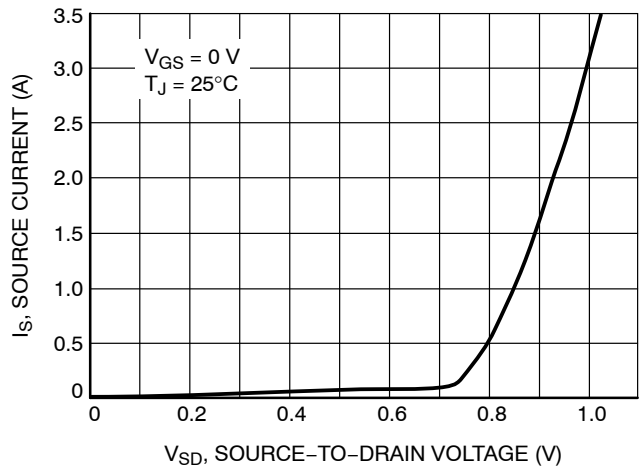


Figure 10. Diode Forward Voltage vs. Current

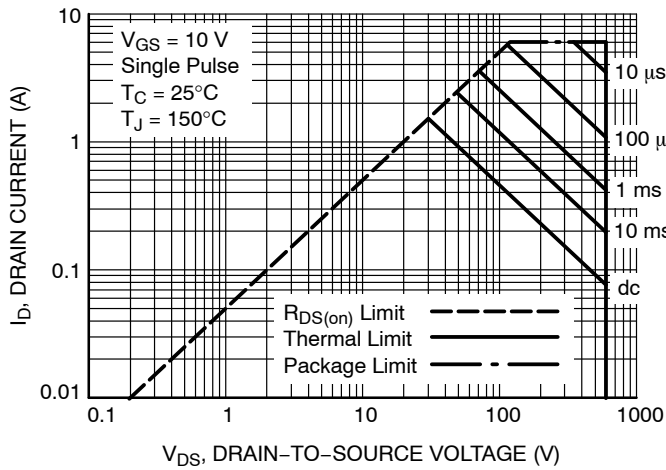


Figure 11. Maximum Rated Forward Biased Safe Operating Area NDD01N60

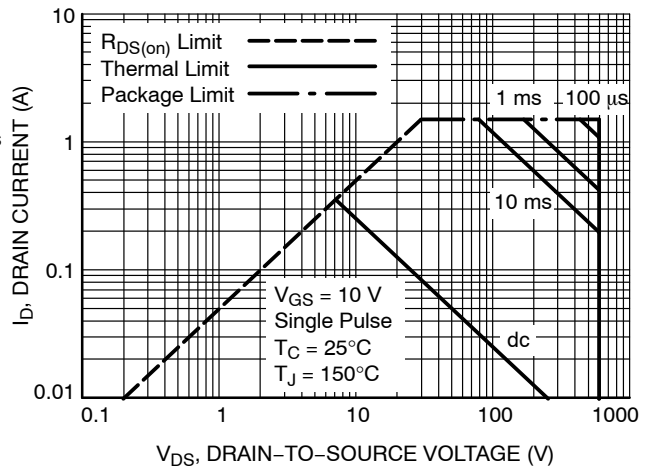


Figure 12. Maximum Rated Forward Biased Safe Operating Area NDT01N60

NDD01N60, NDT01N60

TYPICAL CHARACTERISTICS

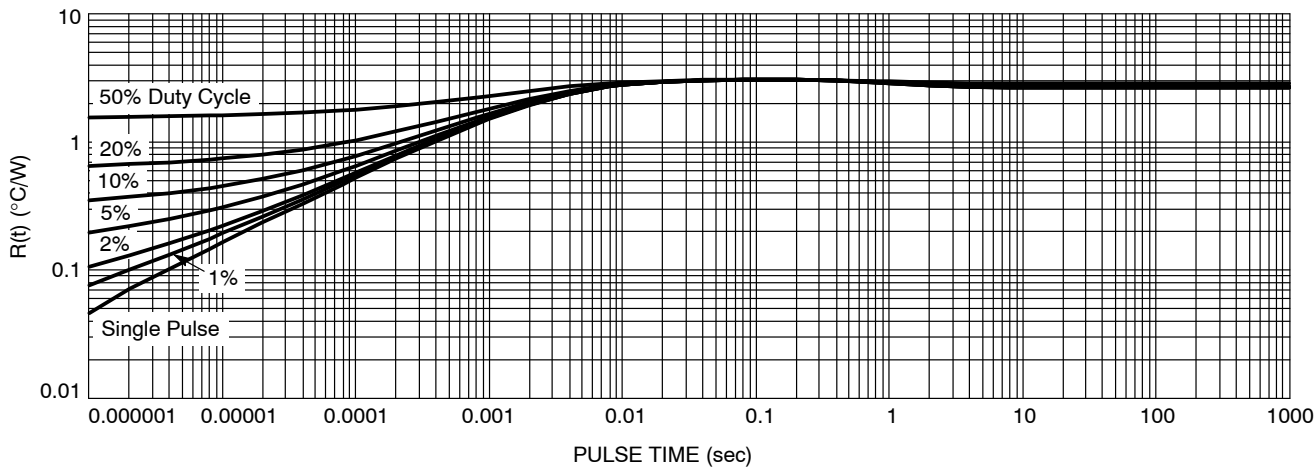


Figure 13. Thermal Impedance (Junction-to-Case) for NDD01N60

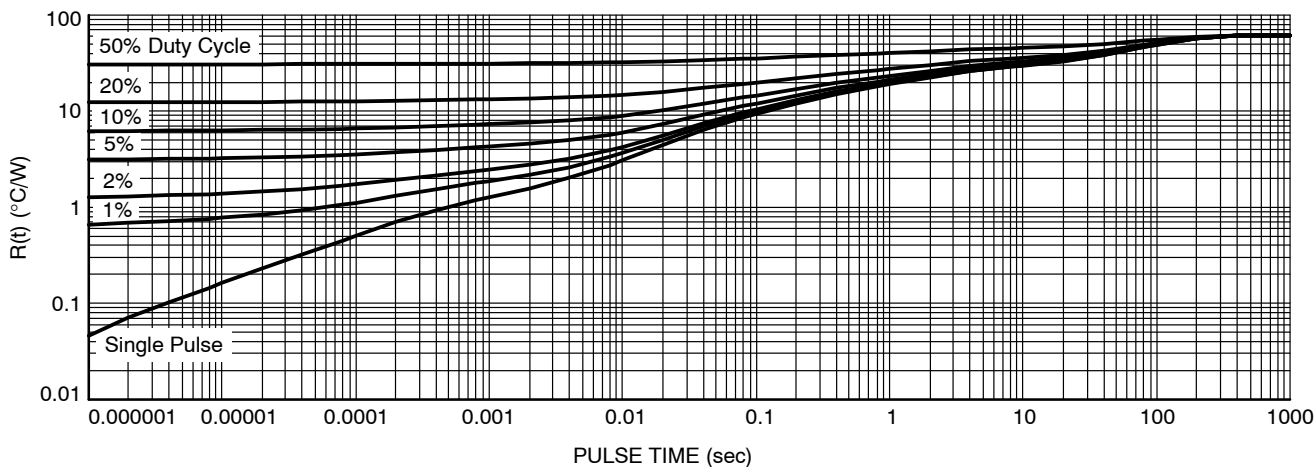


Figure 14. Thermal Impedance (Junction-to-Ambient) for NDT01N60

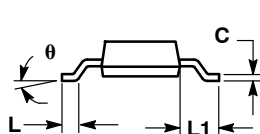
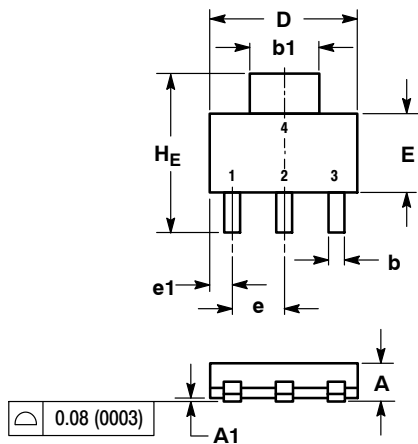
NDD01N60, NDT01N60

PACKAGE DIMENSIONS

SOT-223 (TO-261)

CASE 318E-04

ISSUE N



NOTES:

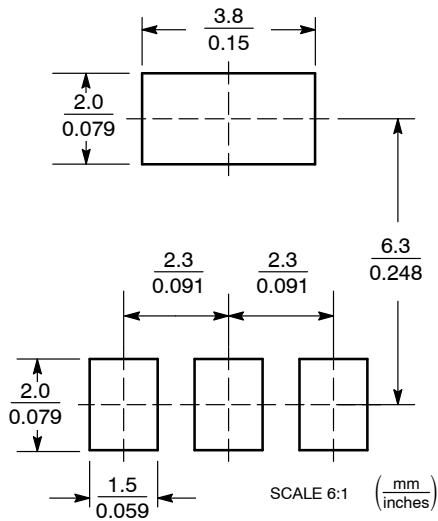
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
c	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
e	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L	0.20	---	---	0.008	---	---
L1	1.50	1.75	2.00	0.060	0.069	0.078
HE	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	---	10°	0°	---	10°

STYLE 3:

- PIN 1. GATE
- DRAIN
- SOURCE
- DRAIN

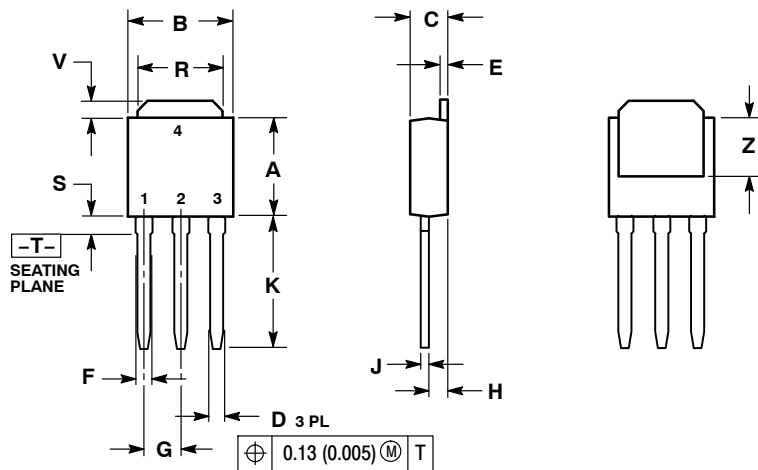
SOLDERING FOOTPRINT



NDD01N60, NDT01N60

PACKAGE DIMENSIONS

IPAK CASE 369D ISSUE C



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

- STYLE 2:
 PIN 1. GATE
 2. DRAIN
 3. SOURCE
 4. DRAIN

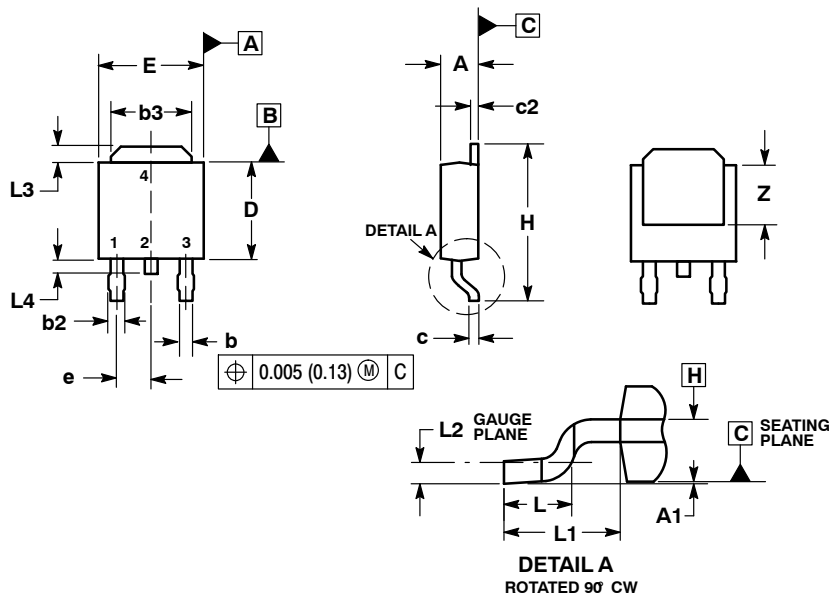
NDD01N60, NDT01N60

PACKAGE DIMENSIONS

DKPAK (SINGLE GAUGE)

CASE 369C-01

ISSUE D



NOTES:

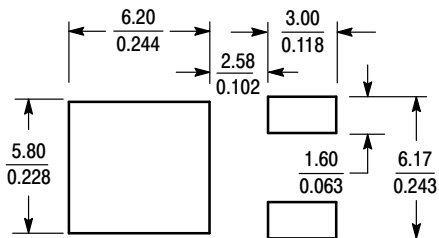
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

STYLE 2:

1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT*



SCALE 3:1 (mm / inches)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marketing.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative